# COMPOSITIONAL VARIATION OF OPTICAL AND REFRACTOMETRIC PARAMETERS OF $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> MIXED CRYSTALS

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Refractive index dispersion in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals with x=0.1; 0.2; 0.3; 0.4 in a broad spectral range is shown to be well described by optical-refractometric relation. The effect of In→Ga cationic substitution upon the refractive index dispersion and molar refraction in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals is studied.

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## 1. Introduction

Crystals of  $(Ga_xIn_{1-x})_2Se_3$  semiconducting solid solutions with 0.02 < x < 0.55 belong to the  $\gamma_1$ -phase of the  $Ga_2Se_3$ -In\_2Se\_3 chalcogenide ternary compounds [1]. They crystallize in hexagonal structure with defect wurtzite symmetry (P6<sub>1</sub> or P6<sub>5</sub> space group). A typical feature of this structure is high concentration of vacancies due to the fact 1/3 of sites in the cation sublattice being empty; these vacancies are the intrinsic defects of the crystal lattice, capable of forming spirals along the *c* axis [1].  $\gamma_1$ -(Ga\_xIn\_{1-x})\_2Se\_3 crystals are characterized by low electronic conductivity ( $\sim 10^{-10} \ \Omega^{-1} \times \text{cm}^{-1}$ ). Photoconductivity in  $\gamma_1$ -phase is almost by three orders higher than in other phases [1]. The crystals possess high optical activity along the optical axis and are promising materials for acousto-optical modulators [2–5]. Some optical properties (Raman scattering, far-infrared reflection spectra, fundamental absorption edge spectra) were presented in [2,6–11]. Refractive index dispersion for both ordinary  $n_o$  and extraordinary  $n_e$  rays in  $\gamma_1$ -(Ga\_xIn\_{1-x})\_2Se\_3 crystals were studied at room temperature by prism technique [2].

Here we report the description of the refractive index dispersion by optical-refractometric (OR) relation and the analysis of the compositional behaviour of some optical and refractometric parameters for  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> mixed crystals with *x*=0.1; 0.2; 0.3; 0.4.

### 2. Theory

It was shown [2] that the experimental values of the refractive indices of  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals in a broad spectral range 0.57÷5 µm are in a good agreement with those calculated using a well known one-term Sellmeier relation. However, deeper physical treatment of the dispersion dependences of the refractive indices can be obtained based on the relationship between the refractive index and the energy gap. A number of empirical and semiempirical relations of such kind are known from the

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literature [12–18]. Among them one should first of all mention the well known empirical Moss  $(n_{\infty}^4 E_g = 95 \text{ eV} [12] \text{ or } n_{\infty}^4 E_g = 107 \text{ eV} [13])$  and Penn [14] relations,

$$n_{\infty}^2 - 1 = E_{pv}^2 / E_g^2, \tag{1}$$

where  $n_{\infty}$  is the refractive index in the long-wavelength spectral range,  $E_g$  is the energy gap,  $E_{pv}$  is the energy of plasma vibrations of valence electrons. Wemple and DiDomenico [15,16] made an attempt to find theoretically a correlation between the refractive index and the energy gap and obtained the relation

$$(n_{\infty}^2 - 1)E_t \approx \frac{2}{3}\beta N_c Z_a N_e, \qquad (2)$$

where  $E_t \approx E_g$ ;  $N_c$  is the coordination number;  $Z_a$  is the formal chemical valence of the anion;  $N_e$  is the total number of valence electrons per anion;  $\beta$  is a constant, equal to  $0.37\pm0.04$  eV for covalent and  $0.26\pm0.04$  eV for ionic crystals. Later, Ravindra et al. [17,18] supposed another empirical relationship

$$n_{\infty} = 4.084 - 0.62E_{g} \,. \tag{3}$$

The above relations describe exactly enough the relationship between  $E_g$  and *n* for different classes of semiconductor materials. However, they do not permit to describe the dispersion dependence of the refractive index. OR relation, proposed in [19], lacks this shortcoming.

#### 3. Results and discussion

OR relation enables to describe the dependence of the refractive index on dispersion on the basis of its relationship to the optical pseudogap  $E_g^*$  and the energy of plasma vibrations of valence electrons  $E_{pv}$  as

$$\frac{1}{3} \frac{n^2(h\nu) + 2}{n^2(h\nu) - 1} = \left(\frac{\eta_s}{2}\right)^s \left(1 + \frac{E_g^*}{E_{p\nu}}\right)^s - \left(\frac{h\nu}{E_s}\right)^s,\tag{4}$$

where  $E_{pv} = 28.82 \sqrt{n_v \rho / \mu}$ ,  $n_v$  is the number of valence electrons per formula unit,  $\rho$  is density,  $\mu$  is molecular mass;  $\eta_s$  and  $E_s$  are adjustment parameters; s=2 for the medium-energy and s=3 for the high-energy parts of the transparency range. The optical pseudogap  $E_g^*$  is the energy position of the absorption edge in semiconductors where direct allowed transitions are masked by exponential absorption tails caused by various types of disordering [20].

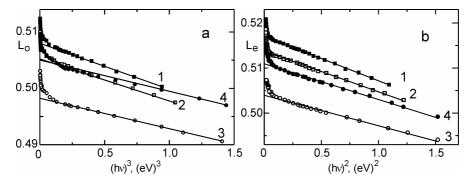


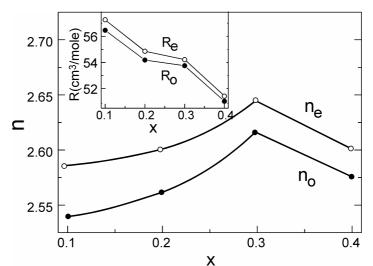
Fig.1. Dependences  $L_0 = f[(h\nu)^3]$  (a) for the refractive index of the ordinary ray and  $L_e = f[(h\nu)^2]$  (b) for the refractive index of the extraordinary ray for  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals with various values of x: 1 - 0.1; 2 - 0.2; 3 - 0.3; 4 - 0.4.

It should be noted that the reliability of the OR relation has been shown for over 150 different non-metallic substances [19]. Hence, Eq. (4) was used to describe the experimental dispersion of the refractive indices of  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals, i. e. the linear dependences  $L=f[(hv)^s]$  (Fig.1) where  $L(hv) \equiv \frac{1}{3} \frac{n^2(hv) + 2}{n^2(hv) - 1}$  being the evidence for the successful description. The dependences  $L=f[(hv)^3]$  are given for the ordinary ray refractive index, and  $L=f[(hv)^2]$  – for the extraordinary one. The values of the adjustment parameters n and E resulting in the best fit between the calculated and

of the adjustment parameters  $\eta_s$  and  $E_s$  resulting in the best fit between the calculated and experimental dependences  $n_o(h\nu)$  and  $n_e(h\nu)$ , are listed in Table 1.

Crystal		ho ,	$E_{pv}$ ,	$E_g^*$ , eV	<i>E</i> <sub>2</sub> ,	$E_3$ ,	$\eta_2$	$\eta_3$
		g/cm <sup>3</sup>	eV	8	eV	eV		
$(Ga_{0.1}In_{0.9})_2Se_3$	0	5.22	15.08	1.982	9.89	5.59	1.263	1.409
	e			1.950	9.66	5.53	1.274	1.418
$(Ga_{0.2}In_{0.8})_2Se_3$	0	5.37	15.45	2.044	10.37	5.62	1.258	1.406
	e			2.012	10.59	6.05	1.268	1.413
$(Ga_{0.3}In_{0.7})_2Se_3$	0	5.41	15.67	2.088	11.02	5.42	1.247	1.399
	e			2.074	11.17	5.48	1.254	1.404
$(Ga_{0.4}In_{0.6})_2Se_3$	0	5.50	15.96	2.188	10.07	5.59	1.253	1.400
	e			2.164	9.46	5.38	1.260	1.405

Table 1. The main optical and refractometric parameters of  $\gamma_1\text{-}(Ga_xIn_{1\text{-}x})_2Se_3$  crystals at room temperature.



**X** Fig. 2. Compositional dependences of the refractive indices  $n_0$  and  $n_e$  at room temperature and  $\lambda = 5 \ \mu m$  for  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals. The inset shows the compositional dependences of molar refractions  $R_0$  and  $R_e$ .

All the crystals are optically positive, since for all of them  $\Delta n = n_e - n_o >0$ . Fig. 2 presents the compositional dependences of the refractive indices  $n_o$  and  $n_e$  for  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals at room temperature and  $\lambda = 5 \mu m$ . With the increase of gallium content the refractive indices increase, reaching maximum at x=0.3, and then decrease. Knowing the compositional dependences of density  $\rho(x)$ ,  $n_o(x)$  and  $n_e(x)$ , the compositional dependences of molar refraction  $R_{o,e}(x)$  were calculated (See the inset to Fig. 2) using the known formula

$$R_{o,e}(x) = \frac{\mu(x)}{\rho(x)} \times \frac{n_{o,e}^2(x) - 1}{n_{o,e}^2(x) + 2}.$$
(5)

It is seen from the inset to Fig. 2 that the increase of gallium content in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals results in the decrease of the molar refraction (electronic polarizability), a feature in the  $R_{o,e}(x)$  dependences being observed at x=0.3. Thus, the anomalous compositional behaviour of the refractive indices in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> is determined by the nonlinear compositional behaviour of density (Table 1) and the anomalous variation of molar refraction (Fig. 2).

#### 3. Conclusions

The dispersion dependences of the refractive indices for ordinary and extraordinary rays in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> crystals with x=0.1, 0.2, 0.3, 0.4 in a broad spectral range are shown to be well described by the optical-refractometric relation linking the dispersion  $n(h\nu)$ , optical pseudogap  $E_g^*$  and the energy of plasma vibrations of the valence electrons  $E_{p\nu}$ . With the increase of Ga content the value of the refractive index increases, reaches a maximum at x=0.3 and then decreases. The anomalous compositional behaviour of the refractive indices in  $\gamma_1$ -(Ga<sub>x</sub>In<sub>1-x</sub>)<sub>2</sub>Se<sub>3</sub> is shown to be determined by the nonlinear compositional behaviour of density and the anomalous variation of molar refraction.

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